IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Lin, et al.	Docket No.:	TSM02-1369
Serial No.:	10/650,445	Art Unit:	2811
Filed:	August 28, 2003	Examiner:	TBD
For:	Ultra-Thin Body Transistor with Recessed Silicide Contacts		

Certificate of Mailing via First Class Mail (37 C.F.R. § 1.8(a))

Date of Deposit: March 17, 2004

I hereby certify that the below listed correspondence is being deposited with the United States Postal Service on the date indicated above as first class mail in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450.

Certificate of Mailing via First Class Mail (1 page)
Information Disclosure Statement (1 page)
Combined Form PTO/SB/08a and 08b (1 page) citing (6) references
Copies of (3) cited references
Return Postcard

Respectfully submitted,

Natalie Swider

Natalie Swider
Legal Assistant

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
Tel: 972-732-1001
Fax: 972-732-9218

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Lin, et al.	Attorney Docket:	TSM02-1369
Filed:	August 28, 2003	Examiner:	TBD
Serial No.:	10/650,445	Art Unit:	2811
For:	Ultra-Thin Body Transistor with Recessed Silicide Contacts		

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed combined form PTO/SB/08a & 08b that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits. However, if a fee is deemed necessary, please charge Deposit Account No. 50-1065 and credit any overpayments to the same.

Respectfully submitted,

March 17, 2004
Date

Steven H. Slater
Attorney for Applicants
Reg. No. 35,361

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
(972) 732-1001 (phone)
(972) 732-9218 (fax)

PTO/SB/08a (08-03)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet	1	of	1

Complete if Known	
Application Number	10/650,445
Filing Date	8/28/2003
First Named Inventor	Lin, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM02-1369

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US-4,998,510	03-12-1991	Rognon	
	2	US-6,137,149	10-24-2000	Kodama	
	3	US-6,420,218 B1	07-16-2002	Yu	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3] - Number[4] - Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	4	Chau, R., et al., "A 50nm Depleted-Substrate CMOS Transistor (DST)," IEDM, pp. 621-624, 2001.	
	5	Choi, Y.K., et al., "Ultrathin-Body SOI MOSFET for Deep-Sub-Tenth Micron Era," IEEE Electron Device Letters, Vol. 21, No. 5, pp. 254-255, May 2000.	
	6	Yeo, Y.C., et al., "Design and Fabrication of 50-nm Thin-Body p-MOSFETs with a SiGe Heterostructure Channel," IEEE Transactions on Electron Devices, Vol. 49, No. 2, pp. 279-286, February 2002.	

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [1]Applicant's unique citation designation number (optional). [2]See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached.